Physics Of Semiconductor Devices Solution

This book presents physics-based electro-thermal models of bipolar power semiconductor devices including their packages, and describes their implementation in MATLAB and Simulink. It is a continuation of our first book Modeling of Bipolar Power Semiconductor Devices. The device electrical models are developed by subdividing the devices into different regions and the operations in each region, along with the interactions at the interfaces, are analyzed using the basic semiconductor physics equations that govern device behavior. The Fourier series solution is used to solve the ambipolar diffusion equation in the lightly doped drift region of the devices. In addition to the external electrical characteristics, internal physical and electrical information, such as junction voltages and carrier distribution in different regions of the device, can be obtained using the models. The instantaneous dissipated power, calculated using the electrical device models, serves as input to the thermal model (RC network with constant and nonconstant thermal resistance and thermal heat capacity, or Fourier thermal model) of the entire module or package, which computes the junction temperature of the device. Once an updated junction temperature is calculated, the temperature-dependent semiconductor material parameters are re-calculated and used with the device electrical model in the next time-step of the simulation. The physics-based electro-thermal models can be used for optimizing device and package design and also for validating extracted parameters of the devices. The thermal model can be used alone for monitoring the junction temperature of a power semiconductor device, and the resulting simulation results used as an indicator of the health and reliability of the semiconductor power device.

A systematic, accessible introduction to III-V semiconductor devices With this handy book, readers seeking to understand semiconductor devices based on III-V materials no longer have to wade through difficult review chapters focusing on a single, novel aspect of the technology. Well-known industry expert William Liu presents here a systematic, comprehensive treatment at an introductory level. Without assuming even a basic course in device physics, he covers the dc and high-frequency operations of all major III-V devices-heterojunction bipolar transistors (HBTs), metal-semiconductor field-effect transistors (MESFETs), and the heterojunction field-effect transistors (HFETs), which include the high electron mobility transistors (HEMTs). An excellent introduction for researchers and circuit designers working on wireless communications equipment, Fundamentals of III-V Devices offers a variety of features, including: * An introductory chapter on the basic properties, growth process, and device physics of III-V materials * Coverage of both dc and high-frequency models, integrating aspects of device physics and circuit design * A discussion of transistor fabrication and device comparison * 55 worked-out examples illustrating design considerations for a given application * 215 figures and end-of-chapter practice problems * Appendices listing parameters for various materials and transistor types

&Quot;An Introduction to Semiconductor Devices by Donald Neamen is designed to provide a fundamental understanding of the characteristics, operations, and limitations of semiconductor devices. In order to meet this goal, the book brings together explanations of fundamental physics of semiconductor materials and semiconductor device physics.". "This new text provides an accessible and modern approach to the material. Aimed at the undergraduate, Neamen keeps coverage of quantum mechanics to a minimum and labels the most advanced material as optional. MOS transistors are covered before bipolar transistors to reflect the dominance of MOS coverage in today's world."--BOOK JACKET.

The advent of the microelectronics technology has made ever-increasing numbers of small devices on a same chip. The rapid emergence of ultra-large-scaled-integrated (ULSI) technology has moved device dimension into the sub-quarter-micron regime and put more than 10 million transistors on a single chip. While traditional closed-form analytical models furnish useful intuition into how semiconductor devices behave, they no longer provide consistently accurate results for all modes of operation of these very small devices. The reason is that, in such devices, various physical mechanisms affect the device performance in a complex manner, and the conventional assumptions (i. e. , one-dimensional treatment, low-level injection, quasi-static approximation, etc.) em ployed in developing analytical models become questionable. Thus, the use of numerical device simulation becomes important in device modeling. Researchers and engineers will rely even more on device simulation for device design and analysis in the future. This book provides comprehensive coverage of device simulation and analysis for various modem semiconductor devices. It will serve as a reference for researchers, engineers, and students who require in-depth, up-to-date information and understanding of semiconductor device physics and characteristics. The materials of the book are limited to conventional and mainstream semiconductor devices; photonic devices such as light emitting and laser diodes are not included, nor does the book cover device modeling, device fabrication, and circuit applications.

Contributed papers of the workshop held at IIT, Madras, in 2003.

Semiconductor Device Physics and Design teaches readers how to approach device design from the point of view of someone who wants to improve devices and can see the opportunity and challenges. It begins with coverage of basic physics concepts, including the physics behind polar heterostructures and strained heterostructures. The book then details the important devices ranging from p-n diodes to bipolar and field effect devices. By relating device design to device performance and then relating device needs to system use the student can see how device design works in the real world.

This book disseminates the current knowledge of semiconductor physics and its applications across the scientific community. It is based on a biennial workshop that provides the participating research groups with a stimulating platform for interaction and collaboration with colleagues from the same scientific community. The book discusses the latest developments in the field of III-nitrides; materials & devices, compound semiconductors, VLSI technology, optoelectronics, sensors, photovoltaics, crystal growth, epitaxy and characterization, graphene and other 2D materials and organic semiconductors.

This textbook describes the basic physics of semiconductors, including the hierarchy of transport models, and connects the theory with the functioning of actual semiconductor devices. Details are worked out carefully and derived from the basic physical concepts, while keeping the internal coherence of the analysis and explaining the different levels of approximation. Coverage includes the main steps used in the fabrication process of integrated circuits: diffusion, thermal oxidation, epitaxy, and ion implantation. Examples are based on silicon due to its industrial importance. Several chapters are included that provide the reader with the quantum-mechanical concepts necessary for understanding the transport properties of crystals. The behavior of crystals incorporating a position-dependent impurity distribution is described, and the different hierarchical transport models for semiconductor devices are derived (from the Boltzmann transport equation to the hydrodynamic and drift-diffusion models). The transport models are then applied to a detailed description of the main semiconductor-device architectures (bipolar, MOS, CMOS), including a number of solid-state sensors. The final chapters are devoted to the measuring methods for semiconductor-device parameters, and to a brief illustration of the scaling rules and numerical methods applied to the design of semiconductor devices.

Modern Semiconductor Devices for Integrated Circuits, First Edition introduces readers to the world of modern semiconductor devices with an emphasis on integrated circuit applications. KEY TOPICS: Electrons and Holes in Semiconductors; Motion and Recombination of Electrons and Holes; Device Fabrication Technology; PN and

Metal–Semiconductor Junctions; MOS Capacitor; MOS Transistor; MOSFETs in ICs—Scaling, Leakage, and Other Topics; Bipolar Transistor. MARKET: Written by an experienced teacher, researcher, and expert in industry practices, this succinct and forward-looking text is appropriate for anyone interested in semiconductor devices for integrated curcuits, and serves as a suitable reference text for practicing engineers.

The awaited revision of Semiconductor Devices: Physics and Technology offers more than 50% new or revised material that reflects a multitude of important discoveries and advances in device physics and integrated circuit processing. Offering a basic introduction to physical principles of modern semiconductor devices and their advanced fabrication technology, the third edition presents students with theoretical and practical aspects of every step in device characterizations and fabrication, with an emphasis on integrated circuits. Divided into three parts, this text covers the basic properties of semiconductor materials, emphasizing silicon and gallium arsenide; the physics and characteristics of semiconductor devices bipolar, unipolar special microwave and photonic devices; and the latest processing technologies, from crystal growth to lithographic pattern transfer.

Analysis and Design of MOSFETs: Modeling, Simulation, and Parameter Extraction is the first book devoted entirely to a broad spectrum of analysis and design issues related to the semiconductor device called metal-oxide semiconductor field-effect transistor (MOSFET). These issues include MOSFET device physics, modeling, numerical simulation, and parameter extraction. The discussion of the application of device simulation to the extraction of MOSFET parameters, such as the threshold voltage, effective channel lengths, and series resistances, is of particular interest to all readers and provides a valuable learning and reference tool for students, researchers and engineers. Analysis and Design of MOSFETs: Modeling, Simulation, and Parameter Extraction, extensively referenced, and containing more than 180 illustrations, is an innovative and integral new book on MOSFETs design technology.

Anticipating a limit to the continuous miniaturization (More-Moore), intense research efforts are being made to co-integrate various functionalities (More-than-Moore) in a single chip. Currently, strain engineering is the main technique used to enhance the performance of advanced semiconductor devices. Written from an engineering applications standpoint, this book encompasses broad areas of semiconductor devices involving the design, simulation, and analysis of Si, heterostructure silicongermanium (SiGe), and III-N compound semiconductor devices. The book provides the background and physical insight needed to understand the new and future developments in the technology CAD (TCAD) design at the nanoscale. Features Covers stressstrain engineering in semiconductor devices, such as FinFETs and III-V Nitride-based devices Includes comprehensive mobility model for strained substrates in global and local strain techniques and their implementation in device simulations Explains the development of strain/stress relationships and their effects on the band structures of strained substrates Uses design of experiments to find the optimum process conditions Illustrates the use of TCAD for modeling strain-engineered FinFETs for DC and AC performance predictions This book is for graduate students and researchers studying solid-state devices and materials, microelectronics, systems and controls, power electronics, nanomaterials, and electronic materials and devices.

The Third Edition of the standard textbook and reference in the field of semiconductor devices This classic book has set the standard for advanced study and reference in the semiconductor device field. Now completely updated and reorganized to reflect the tremendous advances in device concepts and performance, this Third Edition remains the most detailed and exhaustive single source of information on the most important semiconductor devices. It gives readers immediate access to detailed descriptions of the underlying physics and performance characteristics of all major bipolar, field-effect, microwave, photonic, and sensor devices. Designed for graduate textbook adoptions and reference needs, this new edition includes: A complete update of the latest developments New devices such as three-dimensional MOSFETs, MODFETs, resonant-tunneling diodes, semiconductor sensors, quantum-cascade lasers, single-electron transistors, real-space transfer devices, and more Materials completely reorganized Problem sets at the end of each chapter All figures reproduced at the highest quality Physics of Semiconductor Devices, Third Edition offers engineers, research scientists, faculty, and students a practical basis for understanding the most important devices in use today and for evaluating future device performance and limitations. A Solutions Manual is available from the editorial department.

In recent years the mathematical modeling of charge transport in semi conductors has become a thriving area in applied mathematics. The drift diffusion equations, which constitute the most popular model for the simula tion of the electrical behavior of semiconductor devices, are by now mathe matically quite well understood. As a consequence numerical methods have been developed, which allow for reasonably efficient computer simulations in many cases of practical relevance. Nowadays, research on the drift diffu sion model is of a highly specialized nature. It concentrates on the explora tion of possibly more efficient discretization methods (e.g. mixed finite elements, streamline diffusion), on the improvement of the performance of nonlinear iteration and linear equation solvers, and on three dimensional applications. The ongoing miniaturization of semiconductor devices has prompted a shift of the focus of the modeling research lately, since the drift diffusion model does not account well for charge transport in ultra integrated devices. Extensions of the drift diffusion model (so called hydrodynamic models) are under investigation for the modeling of hot electron effects in submicron MOS-transistors, and supercomputer technology has made it possible to employ kinetic models (semiclassical Boltzmann-Poisson and Wigner Poisson equations) for the simulation of certain highly integrated devices.

This textbook provides a theoretical background for contemporary trends in solid-state theory and semiconductor device physics. It discusses advanced methods of quantum mechanics and field theory and is therefore primarily intended for graduate students in theoretical and experimental physics who have already studied electrodynamics, statistical physics, and quantum mechanics. It also relates solid-state physics fundamentals to semiconductor device applications and includes auxiliary results from mathematics and quantum mechanics, making the book useful also for graduate students in electrical engineering and material science. Key Features: Explores concepts common in textbooks on

semiconductors, in addition to topics not included in similar books currently available on the market, such as the topology of Hilbert space in crystals Contains the latest research and developments in the field Written in an accessible yet rigorous manner

Provides an overview of the physical basis of noise in semiconductor devices, and a detailed treatment of numerical noise simulation in small-signal conditions. It presents innovative developments in the noise simulation of semiconductor devices operating in large-signal quasi-periodic conditions.

In the last two decades semiconductor device simulation has become a research area, which thrives on a cooperation of physicists, electrical engineers and mathe maticians. In this book the static semiconductor device problem is presented and analysed from an applied mathematician's point of view. I shall derive the device equations - as obtained for the first time by Van Roosbroeck in 1950 - from physical principles, present a mathematical analysis, discuss their numerical solu tion by discretisation techniques and report on selected device simulation runs. To me personally the most fascinating aspect of mathematical device analysis is that an interplay of abstract mathematics, perturbation theory, numerical analysis and device physics is prompting the design and development of new technology. I very much hope to convey to the reader the importance of applied mathematics for technological progress. Each chapter of this book is designed to be as selfcontained as possible, however, the mathematical analysis of the device problem requires tools which cannot be presented completely here. Those readers who are not interested in the mathemati cal methodology and rigor can extract the desired information by simply ignoring details and proofs of theorems. Also, at the beginning of each chapter I refer to textbooks which introduce the interested reader to the required mathematical concepts.

Market_Desc: · Electrical Engineers· Scientists Special Features: · Provides strong coverage of all key semiconductor devices. Includes basic physics and material properties of key semiconductors· Covers all important processing technologies About The Book: This book is an introduction to the physical principles of modern semiconductor devices and their advanced fabrication technology. It begins with a brief historical review of major devices and key technologies and is then divided into three sections: semiconductor material properties, physics of semiconductor devices and processing technology to fabricate these semiconductor devices.

The 3rd edition of this successful textbook contains ample material for a comprehensive upper-level undergraduate or beginning graduate course, guiding readers to the point where they can choose a special topic and begin supervised research. The textbook provides a balance between essential aspects of solid-state and semiconductor physics, on the one hand, and the principles of various semiconductor devices and their applications in electronic and photonic devices, on the other. It highlights many practical aspects of semiconductors such as alloys, strain, heterostructures, nanostructures, that are necessary in modern semiconductor research but typically omitted in textbooks. Coverage also includes additional advanced topics, such as Bragg mirrors, resonators, polarized and magnetic semiconductors, nanowires, quantum dots, multi-junction solar cells, thin film transistors, carbon-based nanostructures and transparent conductive oxides. The text derives explicit formulas for many results to support better understanding of the topics. The Physics of Semiconductors requires little or no prior knowledge of solid-state physics and evolved from a highly regarded two-semester course. In the third edition several topics are extended and treated in more depth including surfaces, disordered materials, amorphous semiconductors, polarons, thermopower and noise. More than 1800 references guide the reader to historic and current literature including original and review papers and books.

This is a first undergraduate textbook in Solid State Physics or Condensed Matter Physics. While most textbooks on the subject are extremely dry, this book is written to be much more exciting, inspiring, and entertaining.

This book is designed to help readers gain a basic understanding of semiconductor devices and the physical operating principles behind them. This two-fold approach 1) provides the user with a sound understanding of existing devices, and 2) helps them develop the basic tools with which they can later learn about applications and the latest devices. The piece provides one of the most comprehensive treatments of all the important semiconductor devices, and reflects the most current trends in the technology and theoretical understanding of the devices. FEATURES/BENEFITS *NEW--Thoroughly updated to reflect the most current trends in the technology and theoretical understanding of devices. *NEW--Expanded description of silicon Czochralski growth, wafer production, and vapor phase epitaxy (Ch. 1). *NEW--Clearer discussion of chemical bonding, energy band formation and hole transport (Chs. 2, 3 and 4). *NEW--Consolidated coverage of p-n junction diodes and its applications (Ch. 5). *NEW--Greatly expanded/updated discussion of device fabrication processes (Ch. 5 and appendices). *NEW--Earlier discussion of MOS devices (Ch. complementary MOS field effect transistors (MOSFETs) in integrated circuits today. *NEW--Major revision of chapter on Field Effect Transistors (Ch. 6)--Both in the underlying theory as well as discussion of a variety of short channel, high field and hot carrier effects in scaled, ultra-small MOSFETs. Includes extensive discussions of the current-voltage and capacitance-voltage characteristics of these devices--and the information that can be gleaned from such measurements. *NEW--Updated chapter on Bipolar Junction Transistors (BJTs) (Ch. 7)--To reflect current technology. Describes higher-order effects (including the Kirk effect and Webster effect); discusses the Gummel-Poon model (which is more elaborate and physically more accurate than the Ebers-Moll model); and updates the fabrication aspects of BJTs. *NEW--Consolidated coverage of optoelectronic devices in a single chapter (Ch. 8)--Brings the discussion of semiconductor lasers into the same chapter as LEDs and detectors *Reflects the growing importance of optoelectronics. *NEW--Updated coverage of integrated circuits (Ch. concerted shift to CMOS applications, such as logic and memory integrated circuits. *NEW--A section on the insulated gate bipolar transistor (Ch. 11)--A device that is gradually supplanting the semiconductor-controlled rectifier. *NEW--Real data--Wherever feasible, replaces idealized current-voltage and capacitance-voltage plots with real data.

An Introduction to Semiconductor Devices by Donald Neamen provides an understanding of the characteristics, operations and limitations of semiconductor devices. In order to provide this understanding, the book brings together the fundamental physics of the semiconductor

material and the semiconductor device physics. This new text provides an accessible and modern presentation of material. Quantum mechanic material is minimal, and the most advanced material is designated with an icon. This modern approach meands that coverage of the MOS transistor preceeds the material on the bipolar transitor, which reflects the dominance of MOS technology in today's world. Excellent pedagogy is present throughout the book in the form of interesting chapters openers, worked examples, a variety of exercises, key terms, and end of chapter problems.

Numerical simulation is rapidly becoming an important part of the VLSI design process, allowing the engineer to test, evaluate, and optimize various aspects of chip design without resorting to the costly and time-consuming process of fabricating prototypes. This procedure not only accelerates the design process, but also improves the end product, since it is economically feasible to numerically simulate many more options than might otherwise be considered. With the enhanced computing power of today's computers, more sophisticated models are now being developed. This volume contains the proceedings of the AMS-SIAM Summer Seminar on Computational Aspects of VLSI Design, held at the Institute for Mathematics and Its Applications at the University of Minnesota, in the spring of 1987. The seminar featured presentations by some of the top experts working in this area. Their contributions to this volume form an excellent overview of the mathematical and computational problems arising in this area.

This book deals mainly with physical device models which are developed from the carrier transport physics and device geometry considerations. The text concentrates on silicon and gallium arsenide devices and includes models of silicon bipolar junction transistors, junction field effect transistors (JFETs), MESFETs, silicon and GaAs MESFETs, transferred electron devices, pn junction diodes and Schottky varactor diodes. The modelling techniques of more recent devices such as the heterojunction bipolar transistors (HBT) and the high electron mobility transistors are discussed. This book contains details of models for both equilibrium and non-equilibrium transport conditions. The modelling Technique of Small-scale devices is discussed and techniques applicable to submicron-dimensioned devices are included. A section on modern quantum transport analysis techniques is included. Details of essential numerical schemes are given and a variety of device models are used to illustrate the application of these techniques in various fields.

On the the mathematical aspects of the theory of carrier transport in semiconductor devices. The subjects covered include hydrodynamical models for semiconductors based on the maximum entropy principle of extended thermodynamics, mathematical theory of drift-diffusion equations with applications, and the methods of asymptotic analysis.

Physics of Semiconductor Devices covers both basic classic topics such as energy band theory and the gradual-channel model of the MOSFET as well as advanced concepts and devices such as MOSFET short-channel effects, low-dimensional devices and single-electron transistors. Concepts are introduced to the reader in a simple way, often using comparisons to everyday-life experiences such as simple fluid mechanics. They are then explained in depth and mathematical developments are fully described. Physics of Semiconductor Devices contains a list of problems that can be used as homework assignments or can be solved in class to exemplify the theory. Many of these problems make use of Matlab and are aimed at illustrating theoretical concepts in a graphical manner.

Provides first-hand insights into advanced fabrication techniques for solution processable organic electronics materials and devices The field of printable organic electronics has emerged as a technology which plays a major role in materials science research and development. Printable organic electronics soon compete with, and for specific applications can even outpace, conventional semiconductor devices in terms of performance, cost, and versatility. Printing techniques allow for large-scale fabrication of organic electronic components and functional devices for use as wearable electronics, health-care sensors, Internet of Things, monitoring of environment pollution and many others, yet-to-be-conceived applications. The first part of Solution-Processable Components for Organic Electronic Devices covers the synthesis of: soluble conjugated polymers; solution-processable nanoparticles of inorganic semiconductors; high-k nanoparticles by means of controlled radical polymerization; advanced blending techniques yielding novel materials with extraordinary properties. The book also discusses photogeneration of charge carriers in nanostructured bulk heterojunctions and charge carrier transport in multicomponent materials such as composites and nanocomposites as well as photovoltaic devices modelling. The second part of the book is devoted to organic electronic devices, such as field effect transistors, light emitting diodes, photovoltaics, photodiodes and electronic memory devices which can be produced by solution-based methods, including printing and roll-to-roll manufacturing. The book provides in-depth knowledge for experienced researchers and for those entering the field. It comprises 12 chapters focused on: ? novel organic electronics components synthesis and solution-based processing techniques ? advanced analysis of mechanisms governing charge carrier generation and transport in organic semiconductors and devices ? fabrication techniques and characterization methods of organic electronic devices Providing coverage of the state of the art of organic electronics, Solution-Processable Components for Organic Electronic Devices is an excellent book for materials scientists, applied physicists, engineering scientists, and those working in the electronics industry.

This book presents physics-based models of bipolar power semiconductor devices and their implementation in MATLAB and Simulink. The devices are subdivided into different regions, and the operation in each region, along with the interactions at the interfaces, are analyzed using basic semiconductor physics equations that govern their behavior. The Fourier series solution is used to solve the ambipolar diffusion equation in the lightly doped drift region of the devices. In addition to the external electrical characteristics, internal physical and electrical information, such as the junction voltages and the carrier distribution in different regions of the device, can be obtained using the models. Key words: power semiconductor devices; physics-based model; Fourier series solution; drift region, carrier diffusion, transient switching behavior

Special Features *Computer-based exercises and homework problems -- unique to this text and comprising 25% of the total number of problems -- encourage students to address realistic and challenging problems, experiment with what if scenarios, and easily obtain graphical outputs. Problems are designed to progressively enhance MATLAB-use proficiency, so students need not be familiar with MATLAB at the start of your course. Program scripts that are answers to exercises in the text are available at no charge in electronic form (see Teaching Resources below). *Supplement and Review Mini-Chapters after each of the text's three parts contain an extensive review list of terms, test-like problem sets with answers, and detailed suggestions on supplemental reading to reinforce students' learning and help them prepare for exams. *Read-Only Chapters, strategically placed to provide a change of pace during the course, provide informative, yet enjoyable reading for students. *Measurement Details and Results samples offer students a realistic perspective on the seldom-perfect nature of device characteristics, contrary to the way they are often represented in introductory texts. Content Highlig

Particle simulation of semiconductor devices is a rather new field which has started to catch the interest of the world's scientific community. It represents a time-continuous solution of Boltzmann's transport equation, or its quantum mechanical equivalent, and the field equation, without encountering the usual numerical problems associated with the direct solution. The technique is based on first physical principles by following in detail the transport histories of indi vidual particles and gives a profound insight into the physics of semiconductor devices. The method can be applied to devices of any geometrical complexity and material composition. It yields an accurate description of the device, which is not limited by the assumptions made behind the alternative drift diffusion and hydrodynamic models, which represent approximate solutions to the transport equation. While the development of the particle modelling technique has been hampered in the past by the cost of computer time, today this should not be held against using a method which gives a profound physical insight into individual devices and can be used to predict the properties of devices not yet

manufactured. Employed in this way it can save the developer much time and large sums of money, both important considerations for the laboratory which wants to keep abreast of the field of device research. Applying it to al ready existing electronic components may lead to novel ideas for their improvement. The Monte Carlo particle simulation technique is applicable to microelectronic components of any arbitrary shape and complexity.

Electrical Engineering Advanced Theory of Semiconductor Devices Semiconductor devices are ubiquitous in today's world and are found increasingly in cars, kitchens and electronic door locks, attesting to their presence in our daily lives. This comprehensive book provides the fundamentals of semiconductor device theory from basic quantum physics to computer-aided design. Advanced Theory of Semiconductor Devices will improve your understanding of computer simulation of devices through a thorough discussion of basic equations, their validity, and numerical solutions as they are contained in current simulation tools. You will gain state-of-the-art knowledge of devices used in both III–V compounds and silicon technology. Specially featured are novel approaches and explanations of electronic transport, particularly in p—n junction diodes. Close attention is also given to innovative treatments of quantum-well laser diodes and hot electron effects in silicon technology. This in-depth book is written for engineers, graduate students, and research scientists in solid-state electronics who want to gain a better understanding of the principles underlying semiconductor devices.

This book provides an overview of compound semiconductor materials and their technology. After presenting a theoretical background, it describes the relevant material preparation technologies for bulk and thin-layer epitaxial growth. It then briefly discusses the electrical, optical, and structural properties of semiconductors, complemented by a description of the most popular characterization tools, before more complex hetero- and low-dimensional structures are discussed. A special chapter is devoted to GaN and related materials, owing to their huge importance in modern optoelectronic and electronic devices, on the one hand, and their particular properties compared to other compound semiconductors, on the other. In the last part of the book, the physics and functionality of optoelectronic and electronic device structures (LEDs, laser diodes, solar cells, field-effect and heterojunction bipolar transistors) are discussed on the basis of the specific properties of compound semiconductors presented in the preceding chapters of the book. Compound semiconductors form the back-bone of all opto-electronic and electronic devices besides the classical Si electronics. Currently the most important field is solid state lighting with highly efficient LEDs emitting visible light. Also laser diodes of all wavelength ranges between mid-infrared and near ultraviolet have been the enabler for a huge number of unprecedented applications like CDs and DVDs for entertainment and data storage, not to speak about the internet, which would be impossible without optical data communications with infrared laser diodes as key elements. This book provides a concise overview over this class of materials, including the most important technological aspects for their fabrication and characterisation, also covering the most relevant devices based on compound semiconductors. It presents therefore an excellent introduction into this subject not only for students, but also for engineers and scientist who intend to put their focus on this field of science. Market_Desc: · Design Engineers· Research Scientists· Industrial and Electronics Engineering Managers· Graduate Students Special Features: · Completely updated with 30-50% revisions· Will include worked examples and end-of-the-chapter problems (with a solutions manual)· First edition was the most cited work in contemporary engineering and applied science publications (over 12000 citations since 1969) About The Book: This classic reference provides detailed information on the underlying physics and operational characteristics of all major bipolar, unipolar, special microwave, and optoelectronic devices. It integrates nearly 1,000 references to important original research papers and review articles, and includes more than 650 high-quality technical illustrations and 25 tables of material parameters for device analysis.

The new edition of the most detailed and comprehensive single-volume reference on major semiconductor devices The Fourth Edition of Physics of Semiconductor Devices remains the standard reference work on the fundamental physics and operational characteristics of all major bipolar, unipolar, special microwave, and optoelectronic devices. This fully updated and expanded edition includes approximately 1,000 references to original research papers and review articles, more than 650 high-quality technical illustrations, and over two dozen tables of material parameters. Divided into five parts, the text first provides a summary of semiconductor properties, covering energy band, carrier concentration, and transport properties. The second part surveys the basic building blocks of semiconductor devices, including p-n junctions, metal-semiconductor contacts, and metal-insulator-semiconductor (MIS) capacitors. Part III examines bipolar transistors, MOSFETs (MOS field-effect transistors), and other field-effect transistors such as JFETs (junction field-effect-transistors) and MESFETs (metal-semiconductor field-effect transistors). Part IV focuses on negative-resistance and power devices. The book concludes with coverage of photonic devices and sensors, including light-emitting diodes (LEDs), solar cells, and various photodetectors and semiconductor sensors. This classic volume, the standard textbook and reference in the field of semiconductor devices: Provides the practical foundation necessary for understanding the devices currently in use and evaluating the performance and limitations of future devices Offers completely updated and revised information that reflects advances in device concepts, performance, and application Features discussions of topics of contemporary interest, such as applications of photonic devices that convert optical energy to electric energy Includes numerous problem sets, real-world examples, tables, figures, and illustrations; several useful appendices; and a detailed solutions manual Explores new work on leading-edge technologies such as MODFETs, resonant-tunneling diodes, quantum-cascade lasers, single-electron transistors, real-space-transfer devices, and MOS-controlled thyristors Physics of Semiconductor Devices, Fourth Edition is an indispensable resource for design engineers, research scientists, industrial and electronics engineering managers, and graduate students in the field.